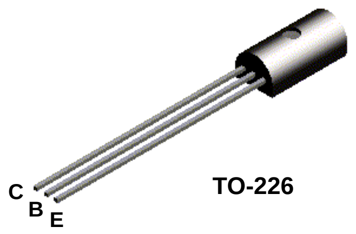
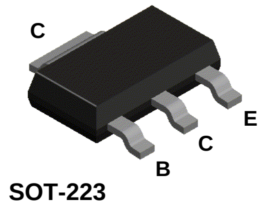
FAIRCHILD
SEMICONDUCTOR ™

Discrete POWER & Signal Technologies

TN6714A NZT6714





NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.5 A. Sourced from Process 37.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	2.0	A
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		TN6714A	*NZT6714	
P_D	Total Device Dissipation Derate above 25°C	1.0 8.0	1.0 8.0	W mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	125	°C/W

*Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm^2.

NPN General Purpose Amplifier
(continued)

Electrical Characteristics

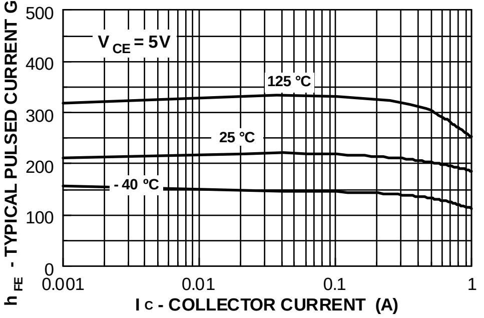
TA= 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	I_C = 10 mA, I_B = 0	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 100 μA, I_E = 0	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 100 μA, I_C = 0	5.0		V
I_{CBO}	Collector-Cutoff Current	V_{CB} = 40 V, I_E = 0		0.1	μA
I_{EBO}	Emitter-Cutoff Current	V_{EB} = 5.0 V, I_C = 0		0.1	μA
ON CHARACTERISTICS					
h_{FE}	DC Current Gain	I_C = 10 mA, V_{CE} = 1.0 V I_C = 100 mA, V_{CE} = 1.0 V I_C = 1.0 A, V_{CE} = 1.0 V	55 60 50	 250	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 1.0 A, I_B = 100 mA		0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C = 1.0 A, V_{CE} = 1.0 V		1.2	V
SMALL SIGNAL CHARACTERISTICS					
h_{fe}	Small-Signal Current Gain	I_C = 50 mA, V_{CE} = 10 V, f = 20 MHz	2.5	25	
C_{cb}	Collector-Base Capacitance	V_{CB} = 10 mA, I_E = 0, f = 1.0 MHz		30	pF

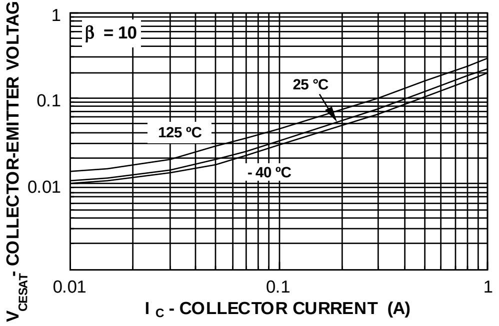
*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%

Typical Characteristics

Typical Pulsed Current Gain vs Collector Current

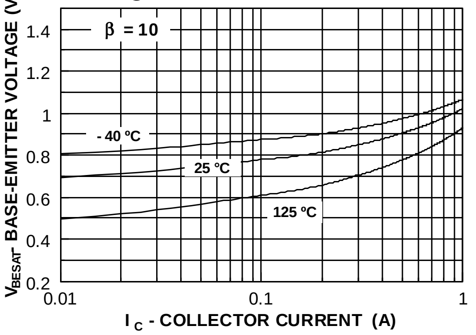


Collector-Emitter Saturation Voltage vs Collector Current

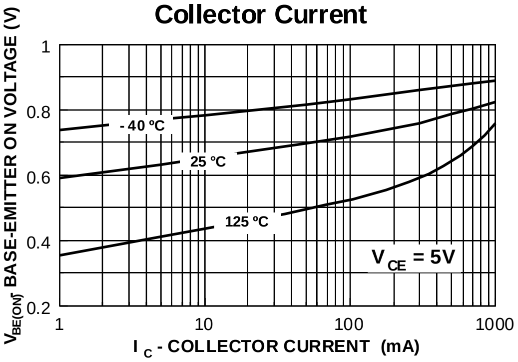


Typical Characteristics (continued)

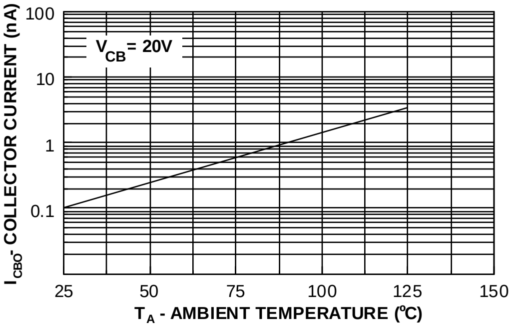
Base-Emitter Saturation Voltage vs Collector Current



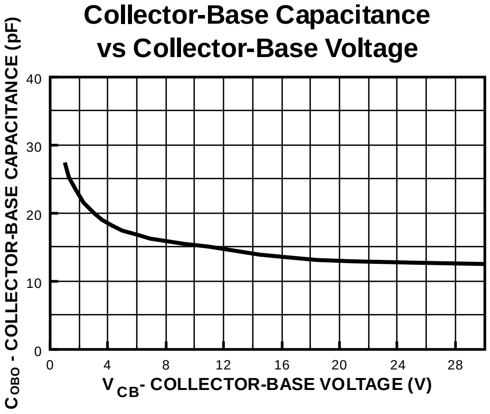
Base-Emitter ON Voltage vs Collector Current



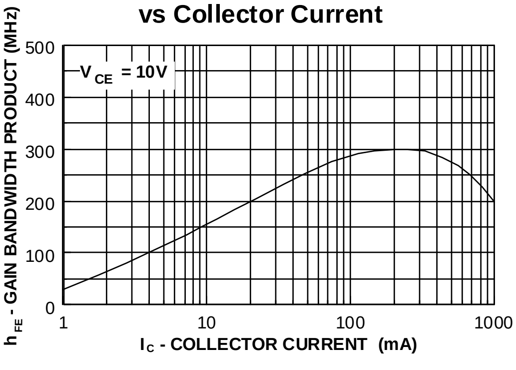
Collector-Cutoff Current vs Ambient Temperature



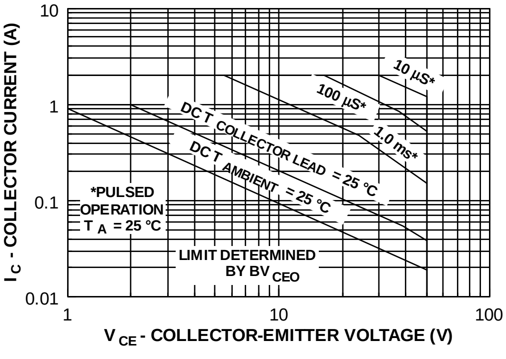
Collector-Base Capacitance vs Collector-Base Voltage



Gain Bandwidth Product vs Collector Current



Safe Operating Area TO-226



Typical Characteristics (continued)